

IN THE CLAIMS:

Please amend claims 5 and 11 as follows:

5. (Amended) The semiconductor memory device according to claim 4, wherein
D1 said silicon nitride layer is patterned to have a same planar shape as the opposing electrode.

11. (Amended) The semiconductor memory device according to claim 10, wherein
D2 said lower part of the insulator laminate includes a silicon nitride layer at an uppermost level, which
is patterned to have a same planar shape as the opposing electrode.